L Number	Hits	Search Text	DB	Time stamp
4	3904	257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.	USPAT; US-PGPUB	2004/09/20 17:10
5	0	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os)) same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	USPAT; US-PGPUB	2004/09/20 17:11
6	16	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (polysilicon with gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os))	USPAT; US-PGPUB	2004/09/20 17:12
7	16	((gate with (platinum pt rhodium rh ruthenium ru iridium ir osmium os)) same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	USPAT; US-PGPUB	2004/09/20 17:15
8	36	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and (gate same ((plug interconnect wiring trace via contact) with (copper cu)) same (source drain))	USPAT; US-PGPUB	2004/09/20 17:24
9	16	(gate with ((plug contact) near2 (copper cu)) with (source drain))	USPAT; US-PGPUB	2004/09/20 17:30
10	30	438/620.ccls. and ((plug contact) with (copper cu))	USPAT; US-PGPUB	2004/09/20 17:32
11	1	((insulat$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch$4 match$4))) and ((atom$2 near (radius radii)) (bond$4 near energy))	EPO; JPO; DERWENT; IBM_TDB	2004/09/20 17:35
12	31	((atom$2 near (radius radii)) (bond$4 near energy)) and (semiconductor silicon si wafer substrate) and (copper cu) and (rhodium rh ruthenium ru iridium ir osmium os platinum pt)	EPO; JPO; DERWENT; IBM_TDB	2004/09/20 17:36
13	7	(semiconductor silicon si wafer substrate) and ((interconnect$5 metal$1is$7 metal$1iz$7) same ((platinum pt) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")) same ((osmium os) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")))	USPAT; US-PGPUB	2004/09/20 17:38
14	271	((atom$2 near (radius radii)) (bond$4 near energy)) and (semiconductor silicon si wafer substrate) and ((copper cu) same (rhodium rh ruthenium ru iridium ir osmium os platinum pt) same (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer"))	USPAT; US-PGPUB	2004/09/20 17:39
15	144	((insulat$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch$4 match$4)) (atom$2 near (radius radii)) (bond$4 near energy)) and ((film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (conduct$5 platinum pt copper cu silver ag gold au rhodium rh ruthenium ru iridium ir osmium os palladium pd cobalt co nickel ni titanium ti))	EPO; JPO; DERWENT; IBM_TDB	2004/09/20 17:59
18	604	(257/412.ccls. 257/413.ccls. 257/762.ccls. 257/766.ccls. 257/768.ccls. 257/769.ccls. 257/774.ccls.) and ((copper cu silver ag gold au platinum pt) same ((rhodium rh ruthenium ru iridium ir osmium os platinum pt) with (palladium pd cobalt co nickel ni titanium ti)))	USPAT; US-PGPUB	2004/09/20 18:06
16	230	(semiconductor silicon si wafer substrate) and ((insulat$4 dielectric oxide dioxide nitride interlayer) with (silicon si)) and ((unit adj cell) (lattice near4 (constant mismatch$4 match$4))) and ((atom$2 near (radius radii)) (bond$4 near energy))	USPAT; US-PGPUB	2004/09/20 18:06

| 17 | 394 | (semiconductor silicon si wafer substrate) and ((interconnect$5 metal$1is$7 metal$1iz$7) same ((copper cu silver ag gold au) near4 (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer")) same ((rhodium rh ruthenium ru iridium ir osmium os platinum pt) with (palladium pd cobalt co nickel ni titanium ti) with (film layer multilayer bilayer trilayer "bi-layer" "tri-layer" "multi-layer") with (element constituent consist$3 compris$3 atom metal))) | USPAT; US-PGPUB | 2004/09/20 18:06 |